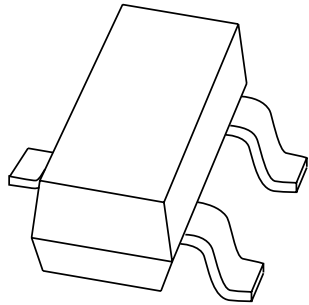


DATA SHEET



PBSS5140T PNP BISS transistor

Product specification

2000 Nov 16

PNP BISS transistor

PBSS5140T

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

- Battery powered units where high current and low power consumption are important.

DESCRIPTION

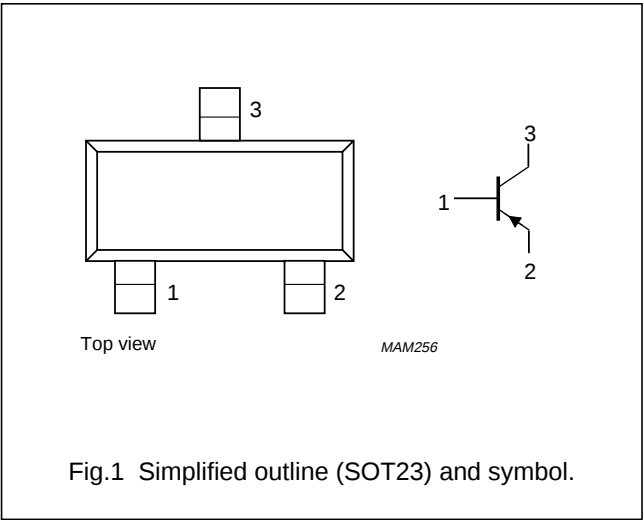
PNP BISS (Breakthrough in Small Signal) transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PBSS5140T	p2H

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–40	V
V _{CEO}	collector-emitter voltage	open base	–	–40	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–1	A
I _{CM}	peak collector current		–	–2	A
I _{BM}	peak base current		–	–1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	300	mW
		T _{amb} ≤ 25 °C; note 2	–	450	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

PNP BISS transistor

PBSS5140T

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	278	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

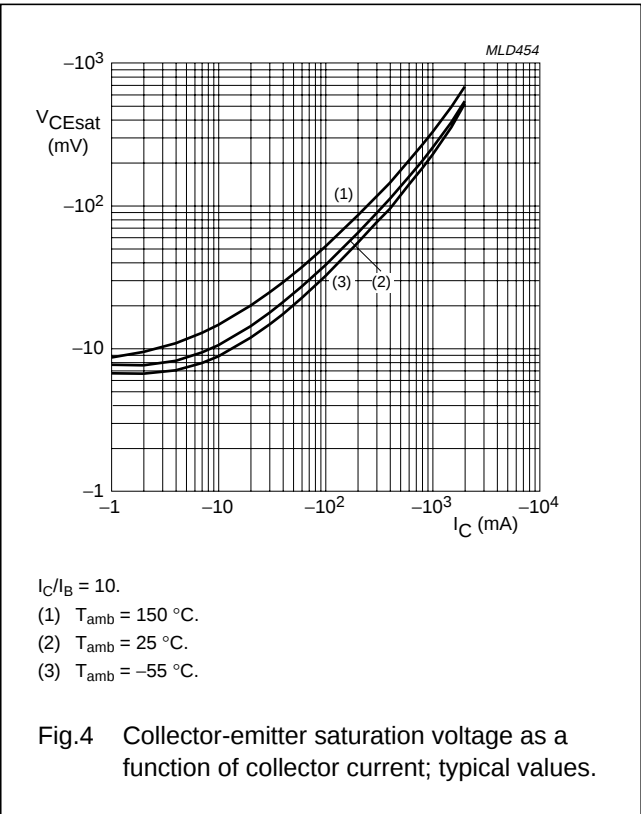
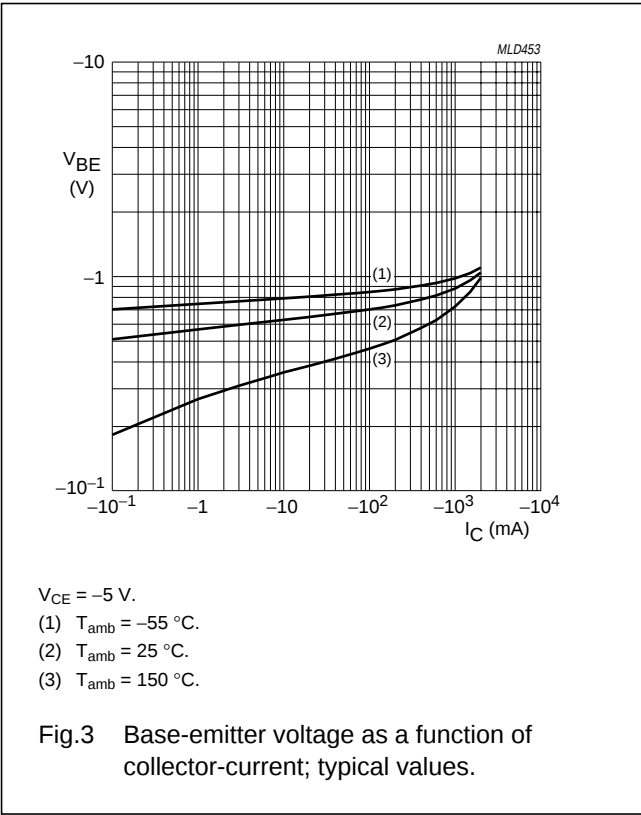
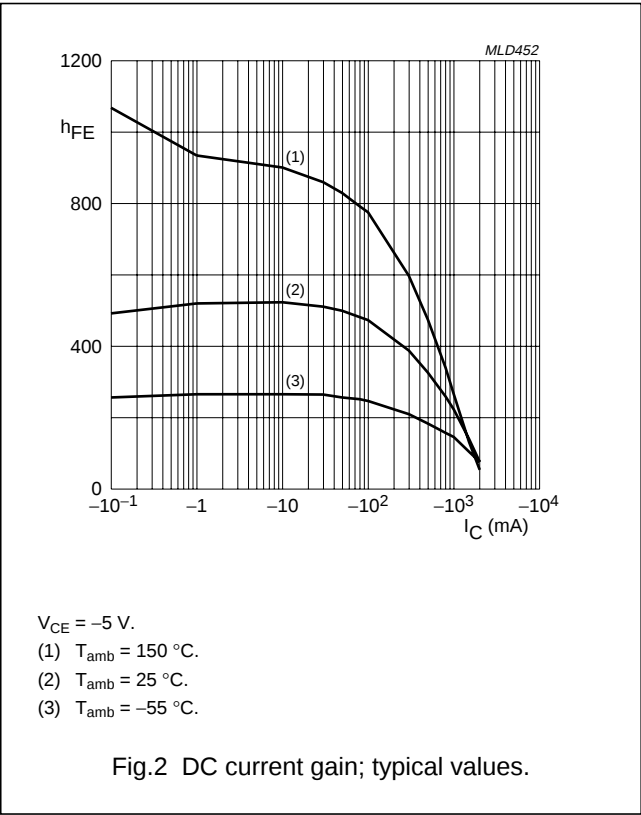
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_E = 0$	–	–100	nA
		$V_{CB} = -40\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–50	μA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0$	–	–100	nA
I_{BEO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; \text{note 1}$			
		$I_C = -1\text{ mA}$	300	–	
		$I_C = -100\text{ mA}$	300	800	
		$I_C = -500\text{ mA}$	250	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -1\text{ A}$	160	–	
		$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–200	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–250	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–1	V
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	150	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ μs}$; $\delta \leq 0.02$.

PNP BISS transistor

PBSS5140T



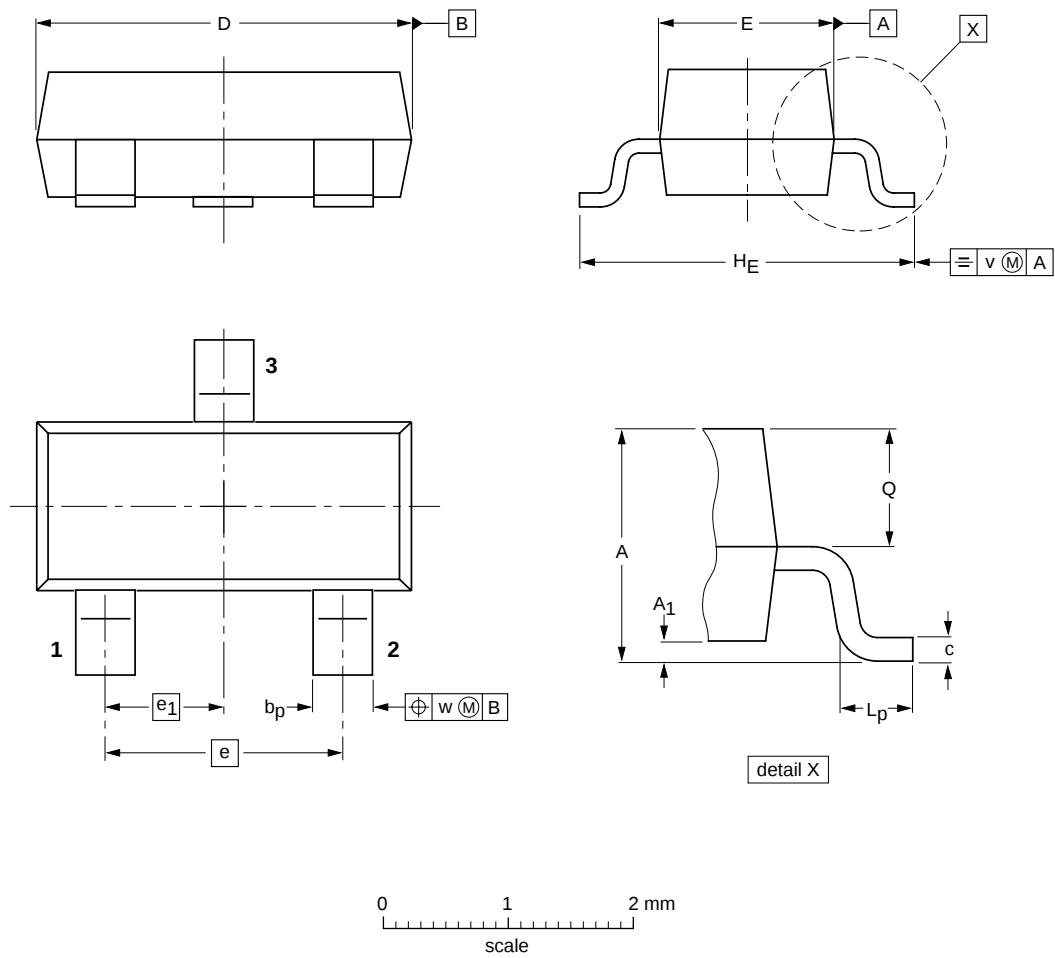
PNP BISS transistor

PBSS5140T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

PNP BISS transistor

PBSS5140T

DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PNP BISS transistor

PBSS5140T

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